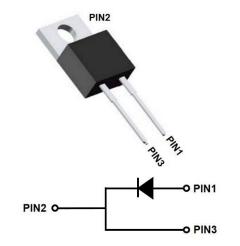


YJD112020PYG5

Silicon Carbide Schottky Diode

V _{RRM}	1200V
I _{F (134°C)}	20A
Q _C	93nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-220AC
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_a=25[°]C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112020PYG5
Reverse voltage (Repetitive peak) @ T _j =25°C	V _{RRM}	V	1200
Reverse voltage (Surge peak) @ Tj=25°C	V _{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _c =25°C		A	41
Continuous forward current @ T _c =134°C	I _F		20
Non-repetitive peak forward surge current @ T_c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	180
Power Dissipation@ T _c =25°C			161
Power Dissipation@ T _c =110°C	P _{TOT}	W	69
i²t Value@ T _c =25°C ,tp=10ms	∫ i²dt	A ² S	162
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

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YJD112020PYG5

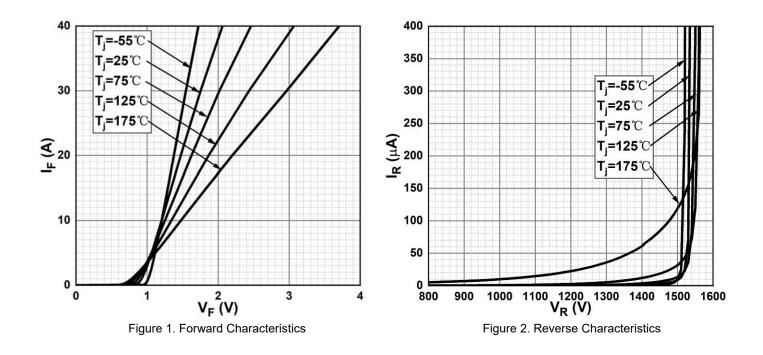
■Electrical Characteristics (Ta=25°C Unless otherwise specified)

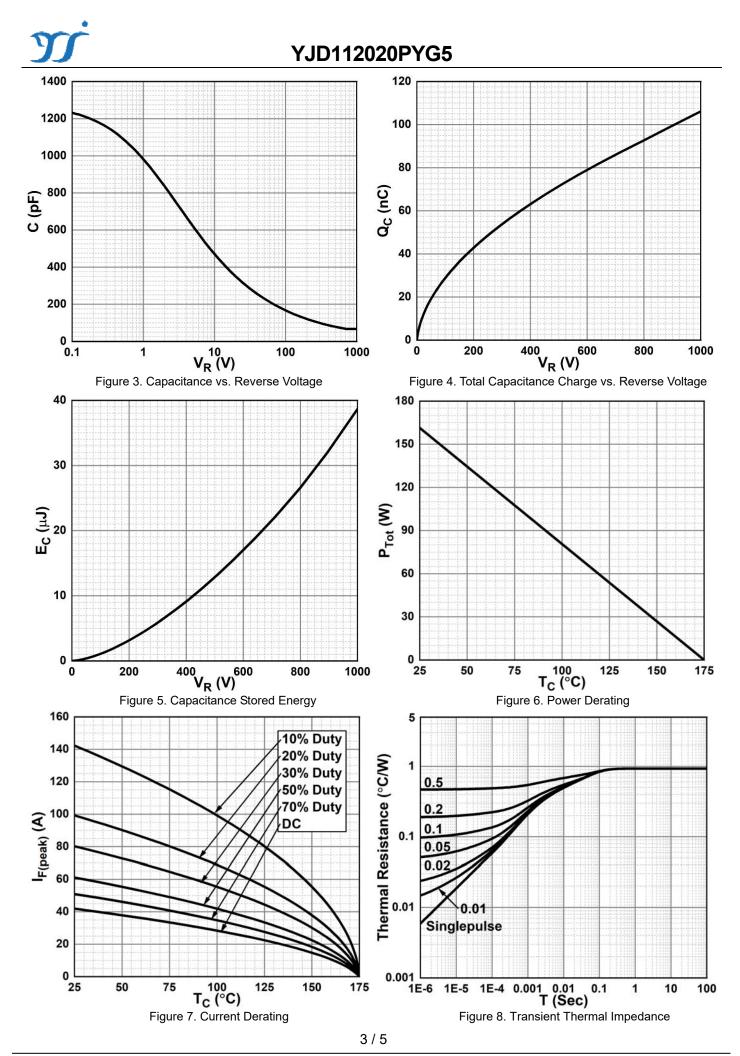
PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.		
	V _F	V	I _F =20A, T _j =25°C	1.48	1.70		
Forward voltage drop			I _F =20A, T _j =175°C	2.20	-		
Deveree europt			V _R =1200V, T _j =25°C	0.5	25		
Reverse current I _R	IR	μA	V _R =1200V, T _j =175°C	30	-		
Total capacitive charge	Qc	nC	V_R =800V, Tj=25°C , Q_C = $\int_0 V^R C(V) dV$	93	-		
	С				V _R =0V, f=1MHZ	1265	-
Total capacitance		pF	V _R =400V, f=1MHZ	87	-		
		V _R =800V, f=1MHZ	67	-			
Capacitance stored energy	Ec	μJ	V _R =800V	26.5	-		

■Thermal Characteristics (Ta=25 °C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C/W	0.93

■Typical Characteristics (Typical)

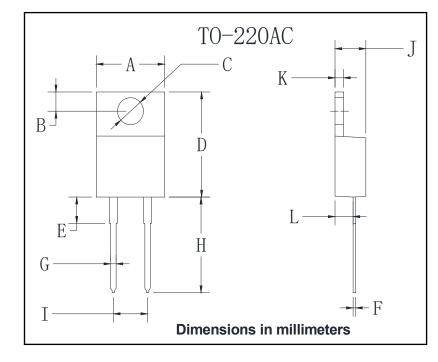




Yangzhou Yangjie Electronic Technology Co., Ltd.



Outline Dimensions



TO-220AC				
Dim	Min	Max		
А	9.95	10.35		
В	2.55	2.95		
С	3.75	4.05		
D	14.95	15.25		
E	3.75	4.25		
F	0.26	0.5		
G	0.68	0.94		
Н	13.3	13.9		
I	4.86	5.26		
J	4.38	4.78		
К	1.14	1.4		
L	2.37	2.79		



YJD112020PYG5

Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

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